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10/091423
03/07/02

PATENT NUMBER and
ISSUE DATE

U.S. UTILITY Patent Application

APPL NUM	FILING DATE	CLASS	SUBCLASS	GAU	EXAMINER
10091423	03/07/2002	257	33C	2826 2811	Erden

****APPLICANTS:** Kawaguchi Yusuke; Yasuhara Norio; Nakamura Kazutoshi; Nakagawa Akio; Ono Syotaro;

****CONTINUING DATA VERIFIED:**

**** FOREIGN APPLICATIONS VERIFIED:**
JAPAN 2001-066707 03/09/2001

PG-PUB DO NOT PUBLISH ☐

RESCIND ☐

Foreign priority claimed ☐ yes ☐ no
35 USC 119 conditions met ☐ yes ☐ no
Verified and Acknowledged Examiners's initials

ATTORNEY DOCKET NO

220471US2S

TITLE : Vertical-type power MOSFET with a gate formed in a trench

U.S. DEPT. OF COMM./PAT. & TM.-PTO-436L (Rev. 12-94)

NOTICE OF ALLOWANCE MAILED		CLAIMS ALLOWED	
		Total Claims	Print Claim for O.G.
Assistant Examiner		DRAWING	
		Sheet Drwg.	Figs. Drwg.
ISSUE FEE		Print Fig.	
Amount Due	Date Paid		
		Primary Examiner	
<input type="checkbox"/> TERMINAL DISCLAIMER		Application Examiner	
		PREPARED FOR ISSUE	
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